# 4V Drive Nch MOS FET **RHK003N06**

### Structure

Silicon N-channel MOS FET

#### Features

1) Low On-resistance. 2) 4V drive.

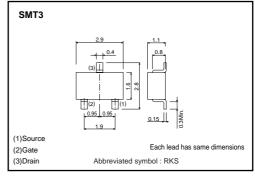
#### Applications

Switching

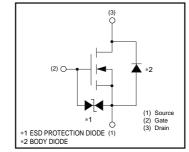
#### Packaging specifications and hre

	Package	Taping
Туре	Code	T146
	Basic ordering unit (pieces)	3000
RHK003N06	0	

#### •External dimensions (Unit : mm)



#### Inner circuit



#### ●Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		VDSS	60	V
Gate-source voltage		Vgss	±20	V
Drain current	Continuous	lo	±300	mA
Drain current	Pulsed	IDP <sup>*1</sup>	±1.2	А
Source current	Continuous	ls	200	mA
(Body diode)	Pulsed	Isp *1	800	mA
Total power dissipation		Pd *2	200	mW
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C
A Decisión o Decto enclosión				

\*1 Pw≤10µs, Duty cycle≤1%
\*2 Each terminal mounted on a recommended land

#### Thermal resistance

Parameter	Symbol	Limits	Unit	
Channel to ambient	Rth(ch-a)*	625	°C/W	

\* Each terminal mounted on a recommended land

# Transistors

# •Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	Igss	-	-	±10	μΑ	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V
Drain-source breakdown voltage	V(BR) DSS	60	-	_	V	I <sub>D</sub> = 1mA, V <sub>GS</sub> =0V
Zero gate voltage drain current	IDSS	-	-	1	μΑ	V <sub>DS</sub> = 60V, V <sub>GS</sub> =0V
Gate threshold voltage	VGS (th)	1.0	-	2.5	V	V <sub>DS</sub> = 10V, I <sub>D</sub> = 1mA
Static drain-source on-state	<b>.</b> .	-	0.7	1.0	Ω	I <sub>D</sub> = 300mA, V <sub>GS</sub> = 10V
resistance	RDS (on)*	-	1.1	1.5	Ω	I <sub>D</sub> = 300mA, V <sub>GS</sub> = 4V
Forward transfer admittance	Y <sub>fs</sub> *	0.2	-	-	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 300mA
Input capacitance	Ciss	-	33	-	pF	V <sub>DS</sub> = 10V
Output capacitance	Coss	-	14	-	pF	V <sub>GS</sub> =0V
Reverse transfer capacitance	Crss	-	9	-	рF	f=1MHz
Turn-on delay time	td (on) *	-	6	_	ns	Vdd≒ 30V
Rise time	tr *	-	5	_	ns	ID= 150mA Vgs= 10V
Turn-off delay time	td (off) *	-	13	_	ns	RL=200Ω
Fall time	t <sub>f</sub> *	-	80	_	ns	Rg=10Ω
Total gate charge	Qg *	-	3	6	nC	V <sub>DD</sub> ≒30V
Gate-source charge	Qgs *	-	0.6	-	nC	Vgs=10V
Gate-drain charge	Q <sub>gd</sub> *	_	0.5	_	nC	ID= 300mA

# •Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsd*	-	-	1.2	V	Is= 300mA, V <sub>GS</sub> =0V
- Data at						

\*Pulsed

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